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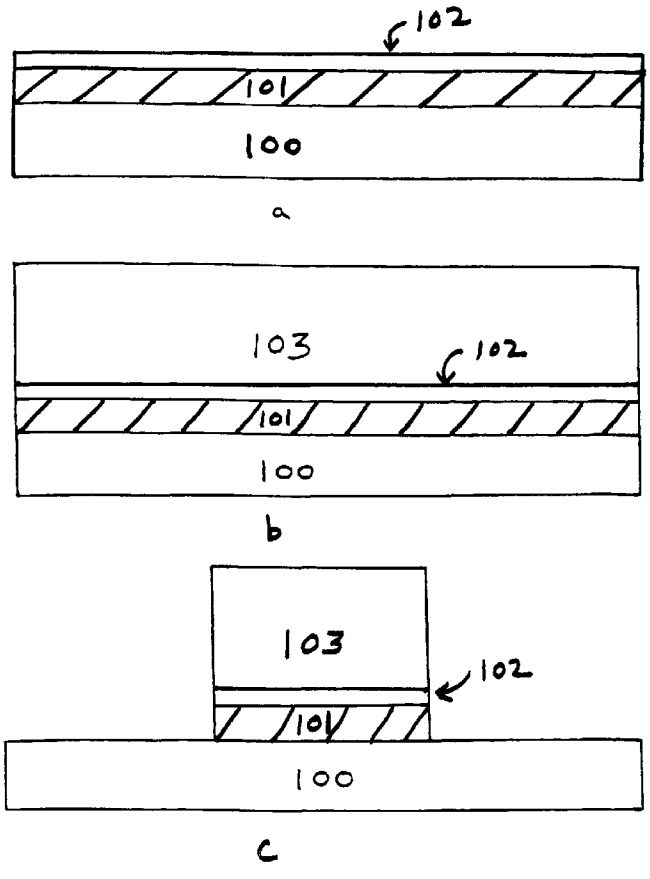
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[Continued on next page]

(54) Title: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC



(57) Abstract: A method for making a semiconductor device is described. That method comprises forming on a substrate (100) a dielectric layer (101) that has a dielectric constant that is greater than the dielectric constant of silicon dioxide. An insulating layer (102), which is compatible with the dielectric layer and a gate electrode to be formed on the insulating layer, is formed on the dielectric layer, and a gate electrode (103) is then formed on the insulating layer.

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